

SEMITOP<sup>®</sup>4

### 3-phase bridge rectifier + brake chopper + 3-phase bridge inverter **SK 50 DGDL 126 T**

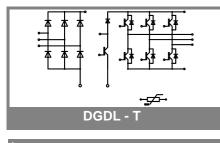
Target Data

#### Features

- One screw mounting module
- Fully compatible with SEMITOP<sup>®</sup>1,2,3
- Improved thermal performances
  by aluminium oxide substrate
- Trench IGBT technology
- CAL technology free-wheeling diode
- Integrated NTC temperature sensor

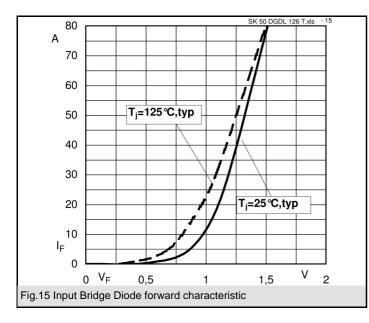
### **Typical Applications**

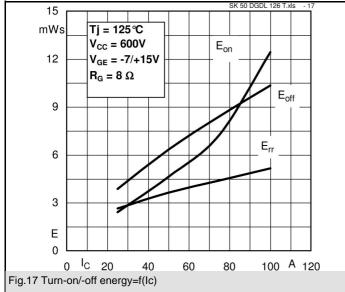
- Inverter up to 28 kVA
- Typ. motor power 15 kW
- 1)  $V_{ce,sat}$ ,  $V_f$  = chip level value
- For IGBT chopper diagrams please refer to SK35DGDL126T

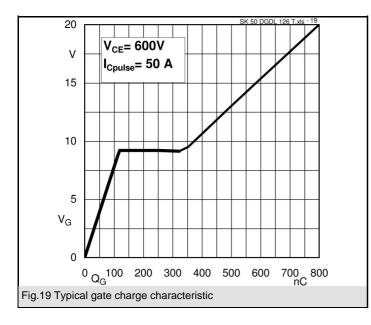


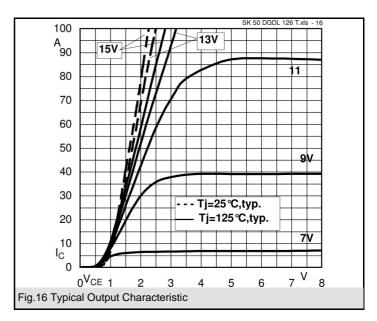
Absolute	Maximum Ratings	Ts = 25 °C, unless otherwise s	Ts = 25 °C, unless otherwise specified						
Symbol	Conditions	Values	Units						
IGBT - Inverter. For IGBT chopper maximum ratings, please refer to									
SK35DGDL126T									
V <sub>CES</sub>		1200	V						
I <sub>C</sub>	T <sub>s</sub> = 25 (70) °C	68 (52)	Α						
I <sub>CRM</sub>	$I_{CRM} = 2 \times I_{Cnom}, t_p = 1 \text{ ms}$	100	Α						
V <sub>GES</sub>		± 20	V						
Т <sub>ј</sub>		-40 +150	°C						
Diode - Ir	verter,Chopper								
I <sub>F</sub>	T <sub>s</sub> = 25 (70) °C	62 (46)	Α						
I <sub>FRM</sub>	$I_{FRM} = 2xI_{Fnom}, t_p = 1 \text{ ms}$	100	А						
T <sub>j</sub>		-40 +150	°C						
Rectifier	•	<b>-</b>	•						
V <sub>RRM</sub>		1600	V						
I <sub>F</sub>	T <sub>s</sub> = 70 °C	61	А						
I <sub>FSM</sub> / I <sub>TSM</sub>	t <sub>p</sub> = 10 ms , sin 180 ° ,T <sub>i</sub> = 25 °C	700	А						
I <sup>2</sup> t	t <sub>p</sub> = 10 ms , sin 180 ° ,T <sub>i</sub> = 25 °C	2400	A²s						
T <sub>j</sub>		-40 +150	°C						
T <sub>sol</sub>	Terminals, 10 s	260	°C						
T <sub>stg</sub>		-40 +125	°C						
V <sub>isol</sub>	AC, 1 min. / 1 s	2500 / 3000	V						

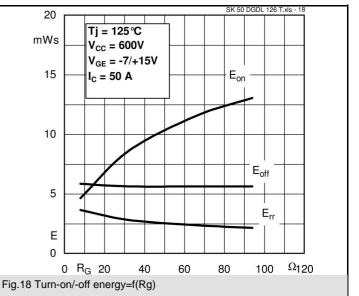
Characteristics Ts = 25 °C, unless otherwise spec					ecified			
Symbol	Conditions	min.	typ.	max.	Units			
IGBT - Inverter. For IGBT chopper electrical characteristics, please refer to								
SK35DGE		i.						
V <sub>CEsat</sub>	I <sub>C</sub> = 50 A, T <sub>j</sub> = 25 (125) °C		1,7 (2)	2,15 (2,45)	V			
V <sub>GE(th)</sub>	$V_{GE} = V_{CE}, I_C = 2 \text{ mA}$	5	5,8	6,5	V			
V <sub>CE(TO)</sub>	$T_j = 25 °C (125) °C$		1 (0,9)	1,2 (1,1)	V			
r <sub>T</sub>	$T_{j} = 25 \text{ °C} (125) \text{ °C}$		14 (22)	19 (27)	mΩ nF			
C <sub>ies</sub>	V <sub>CE</sub> = 25 V <sub>GE</sub> = 0 V, f = 1 MHz V <sub>CE</sub> = 25 V <sub>GE</sub> = 0 V, f = 1 MHz		3,7 0,18		nF			
C <sub>oes</sub> C <sub>res</sub>	$V_{CE} = 25 V_{GE} = 0 V, f = 1 MHz$		0,10		nF			
	$v_{CE} = 25$ $v_{GE} = 0$ $v_{r} = 1$ with 2		0,10		K/W			
R <sub>th(j-s)</sub>	•		,					
t <sub>d(on)</sub>	under following conditions		115 28		ns			
t <sub>r</sub>	V <sub>CC</sub> = 600 V, V <sub>GE</sub> = ± 15 V I <sub>C</sub> = 50 A, T <sub>i</sub> = 125 °C		20 509		ns ns			
t <sub>d(off)</sub> t <sub>f</sub>	$R_{Gon} = R_{Goff} = 8 \Omega$		100		ns			
Կ E <sub>on</sub>	inductive load		4,6		mJ			
E <sub>off</sub>			6,3		mJ			
			0,0		1110			
		1	4 05 (4 05)					
V <sub>F</sub> = V <sub>EC</sub>	I <sub>F</sub> = 50 A, T <sub>j</sub> = 25(125) °C T <sub>i</sub> = 25 °C (125) °C		1,35 (1,35)		V V			
V <sub>(TO)</sub>	$T_{i} = 25 °C (125) °C$ $T_{i} = 25 °C (125) °C$		0,95 (0,85) 8 (10)		mΩ			
r <sub>T</sub>	1		0 (10) 1		K/W			
R <sub>th(j-s)</sub>	per diode				-			
	under following conditions		30		A			
Q <sub>rr</sub>	$I_{\rm F} = 50 \text{ A}, V_{\rm R} = 600 \text{ V}$		10		μC mJ			
Err	$V_{GE} = 0 V, T_j = 125 °C$	3,6						
	di <sub>F/dt</sub> = 500 A/µs							
Diode - R								
V <sub>F</sub>	$I_F = 35 \text{ A}, T_j = 25() ^{\circ}\text{C}$		1,1		V			
V <sub>(TO)</sub>	$T_{j} = 150 \ ^{\circ}C$		0,8		V			
r <sub>T</sub>	$T_{j} = 150 \ ^{\circ}C$	11 0,9			mΩ			
R <sub>th(j-s)</sub>	per diode		K/W					
Temperat	ur sensor							
R <sub>ts</sub>	5 %, T <sub>r</sub> = 25 (100 ) °C	5000(493)			Ω			
Mechanic	al data							
w			60		g			
M <sub>s</sub>	Mounting torque	2,5		2,75	Nm			
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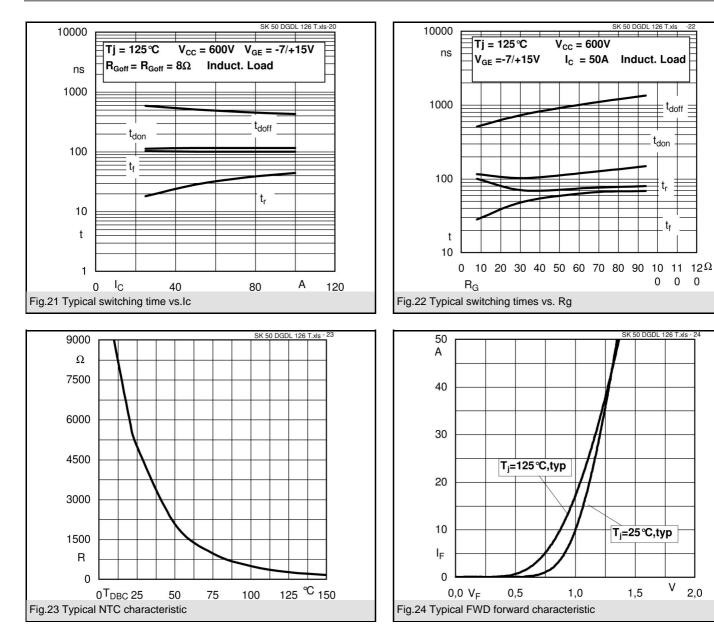








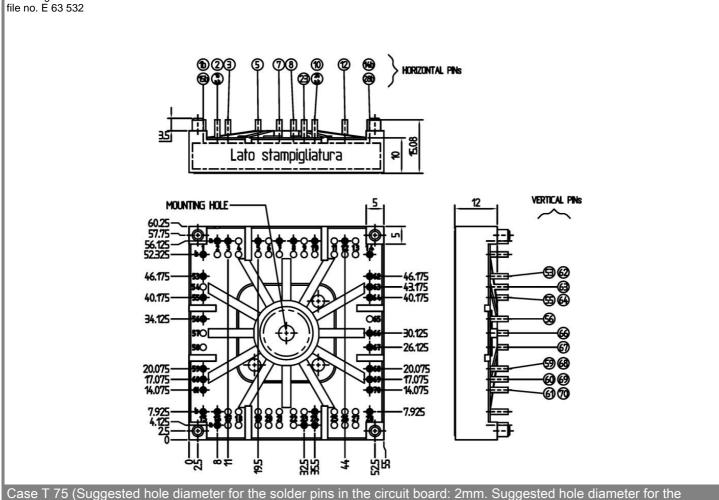




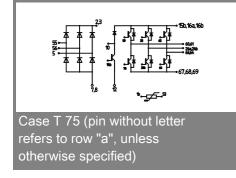
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#### UL recognized

Dimensions in mm



Case T 75 (Suggested hole diameter for the solder pins in the circuit board: 2mm. Suggested hole diameter for the mounting pins in the circuit board: 3,6mm )



This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

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